

Appl. No. 09/754,264  
Amendment and/or Response  
Reply to Office Action of November 19, 2004

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**Amendments to the Claims:**

A clean version of the entire set of pending claims (including amendments to the claims, if any) is submitted herewith per 37 CFR 1.121(c) (3). This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

10. (Previously Presented) A method of depositing a wiring thin film over a semiconductor substrate, the method comprising:

providing a  $\text{Al}_3\text{Ti}$  target;

providing a substrate;

forming a Ti layer over said substrate;

sputter depositing an  $\text{Al}_3\text{Ti}$  layer on said Ti layer using said  $\text{Al}_3\text{Ti}$  target;

and annealing said substrate at a temperature of at least 400 °C to

promote absorption of Si into said  $\text{Al}_3\text{Ti}$  layer.

11. (Previously Presented) A method as recited in claim 10, wherein an Al layer is deposited on said  $\text{Al}_3\text{Ti}$  layer.

12. (Previously Presented) A method as recited in claim 10, further comprising pattern-etching said Al layer thereby forming a wiring pattern.

13. (Previously Presented) A method as recited in claim 10, wherein the method further comprises forming an insulating layer between said substrate and said  $\text{Al}_3\text{Ti}$  layer.

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14. (Currently Amended) A method of forming a wiring film, the method comprising:  
providing a substrate;  
depositing a Ti layer over said substrate;  
depositing an Al-Si-Cu layer on said Ti layer, which forms an Al<sub>3</sub>Ti on  
said Ti layer; and  
pattern etching an Al layer, which forms beneath said Al-Si-Cu layer;  
and  
after the depositing of the Al-Si-Cu layer, annealing the substrate at a temperature of  
at least 400 °C.
15. (Previously Presented) A method as recited in claim 14, wherein said Al-Si-Cu  
layer is deposited at a temperature of at least 400 °C.
16. (Cancelled)
17. (Previously Presented) A method of forming a wiring film, the method  
comprising:  
providing a substrate;  
depositing an Al<sub>3</sub>Ti layer over said substrate;  
depositing an Al layer on said Al<sub>3</sub>Ti layer; and  
pattern etching said Al layer; and  
after the depositing of the Al layer, annealing the substrate at a temperature of at  
least 400 °C.
18. (Previously Presented) A method as recited in claim 17, wherein said Al layer is  
deposited at a temperature of at least 400 °C.
19. (Cancelled)

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20. (Previously Presented) A method as recited in claim 17, wherein said  $\text{Al}_3\text{Ti}$  layer is deposited at a temperature of at least 400 °C.

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